

10.10 Consider a MOS device with a p-type silicon substrate with $N_a = 2 \times 10^{16} \text{ cm}^{-3}$. The oxide thickness is $t_{ox} = 15 \text{ nm} = 150 \text{ \AA}$ and the equivalent oxide charge is $Q'_{ss} = 7 \times 10^{10} \text{ cm}^{-2}$. Calculate the threshold voltage for (a) an n^+ polysilicon gate, (b) a p^+ polysilicon gate, and (c) an aluminum gate.

➤ Also, find $|Q'_{SD}(\text{max})|$ and C_{ox} .

From Table B.4, $n_i = 1.5 \times 10^{10} \text{ cm}^{-3}$, & $\epsilon_r = 11.7$ silicon

From Table B.6, $\epsilon_r = 3.9$ for SiO_2 @ 300K

$$V_t = \frac{k_B T}{e} = \frac{8.617333 \times 10^{-5} \text{ eV/K} (300 \text{ K})}{e} = 0.025852 \text{ V}$$

$$\begin{aligned} \text{Per (10.4), } \phi_{sp} &= V_t \ln\left(\frac{N_a}{n_i}\right) = 0.025852 \ln\left(\frac{2 \times 10^{16}}{1.5 \times 10^{10}}\right) \\ &= 0.364596 \text{ V} \end{aligned}$$

$$\begin{aligned} \text{Per (10.6), } x_{dT} &= \left\{ \frac{4 \epsilon_s \phi_{sp}}{e N_a} \right\}^{1/2} \\ &= \left\{ \frac{4 (11.7) 8.8541878 \times 10^{-12} (0.364596)}{1.602176634 \times 10^{-19} (2 \times 10^{22})} \right\}^{1/2} \\ &= 2.171365 \times 10^{-7} \text{ m} \end{aligned}$$

$$\begin{aligned} \text{Per (10.27), } |Q'_{SD}(\text{max})| &= e N_a x_{dT} \\ &= 1.6022 \times 10^{-19} (2 \times 10^{22}) (2.1714 \times 10^{-7}) \\ |Q'_{SD}(\text{max})| &= 6.95782 \times 10^{-4} \frac{\text{C}}{\text{m}^2} = 6.958 \times 10^{-8} \frac{\text{C}}{\text{cm}^2} \end{aligned}$$

$$\begin{aligned} \text{Per (10.1), } C' = \frac{\epsilon}{d} \Rightarrow C_{ox} &= \frac{\epsilon_{ox}}{t_{ox}} = \frac{3.9 (8.8541878 \times 10^{-12})}{15 \times 10^{-9}} \\ C_{ox} &= 2.30209 \times 10^{-3} \frac{\text{F}}{\text{m}^2} = 2.3021 \times 10^{-7} \frac{\text{F}}{\text{cm}^2} \end{aligned}$$

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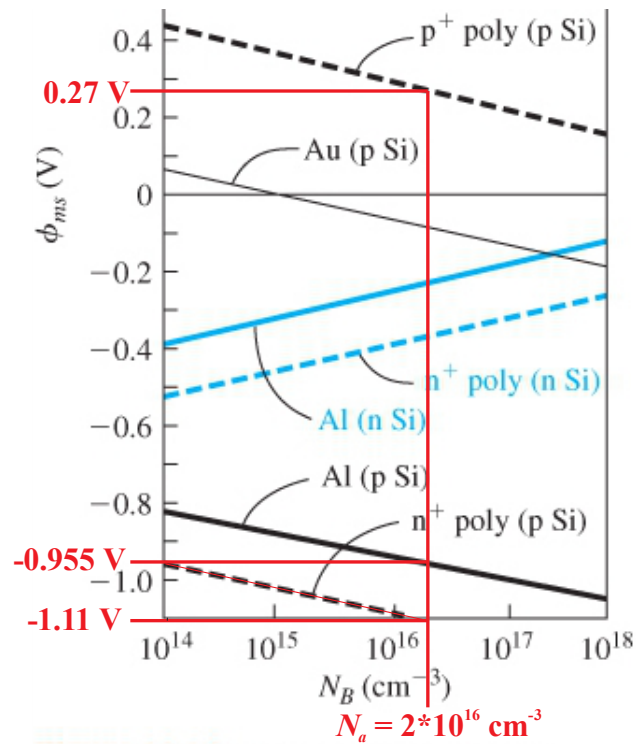


Figure 10.16 | Metal–semiconductor work function difference versus doping

Per (10.31a), $V_{TN} = \frac{|Q_{SD}'(\max)|}{C_{ox}} - \frac{Q_{SS}'}{C_{ox}} + \phi_{ms} + 2\phi_{SP}$

a) Per Fig 10.16, $\phi_{ms} = -1.11$ V for n\$^+\$ poly

$$V_{TN} = \frac{6.95782 \times 10^{-8}}{2.30209 \times 10^{-7}} - \frac{1.6021766 \times 10^{-19} (7 \times 10^{10})}{2.30209 \times 10^{-5}} - 1.11 + 2(0.3646)$$

$$= 0.30224 - 0.04872 - 1.11 + 0.72919$$

$$\underline{\underline{V_{TN} = -0.127 \text{ V}}}$$

b) Per Fig 10.16, $\phi_{ms} = 0.27$ V for p\$^+\$ poly

$$V_{TN} = 0.30224 - 0.04872 + 0.27 + 0.72919 \Rightarrow \underline{\underline{V_{TN} = 1.25 \text{ V}}}$$

c) Per Fig 10.16, $\phi_{ms} = -0.955$ V for Al

$$V_{TN} = 0.30224 - 0.04872 - 0.955 + 0.72919 \Rightarrow \underline{\underline{V_{TN} = 0.028 \text{ V}}}$$